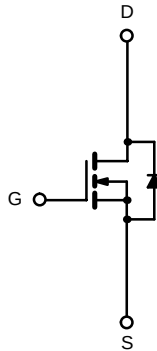
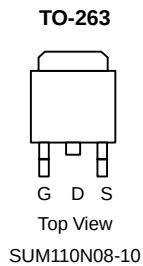




N-Channel 75-V (D-S) MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A)
75	0.010 @ $V_{GS} = 10$ V	110



N-Channel MOSFET

FEATURES

- TrenchFET® Power MOSFET
- New Low Thermal Resistance Package

APPLICATIONS

- Automotive
 - Boardnet 42-VEP and ABS
 - Motor Drives
- High Current
- DC/DC Converters

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	75	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current ($T_J = 175^\circ\text{C}$)	$T_C = 25^\circ\text{C}$	I_D	110	A
	$T_C = 125^\circ\text{C}$		63 ^a	
Pulsed Drain Current		I_{DM}	350	
Avalanche Current		I_{AR}	75	mJ
Repetitive Avalanche Energy ^a		E_{AR}	280	
Maximum Power Dissipation ^a	$T_C = 25^\circ\text{C}$	P_D	200 ^b	W
	$T_A = 25^\circ\text{C}$ ^c		3.7	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 175	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Limit	Unit
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	40	$^\circ\text{C/W}$
Junction-to-Case		R_{thJC}	0.75	

Notes

- Duty cycle $\leq 1\%$.
- See SOA curve for voltage derating.
- When mounted on 1" square PCB (FR-4 material).

SPECIFICATIONS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{DS} = 0 V, I _D = 250 μA	75			V
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2.5		4.0	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V			1	μA
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 125°C			50	
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 175°C			250	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	120			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = 10 V, I _D = 30 A		0.0055	0.010	Ω
		V _{GS} = 10 V, I _D = 30 A, T _J = 125°C			0.0185	
		V _{GS} = 10 V, I _D = 30 A, T _J = 175°C			0.0245	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 30 A	30			S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		5250		pF
Output Capacitance	C _{oss}			700		
Reverse Transfer Capacitance	C _{rss}			310		
Total Gate Charge ^c	Q _g	V _{DS} = 35 V, V _{GS} = 10 V, I _D = 110 A		90	165	nC
Gate-Source Charge ^c	Q _{gs}			24		
Gate-Drain Charge ^c	Q _{gd}			27		
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 35 V, R _L = 0.4 Ω I _D ≅ 110 A, V _{GEN} = 10 V, R _G = 2.5 Ω		20	30	ns
Rise Time ^c	t _r			100	150	
Turn-Off Delay Time ^c	t _{d(off)}			45	70	
Fall Time ^c	t _f			75	115	
Source-Drain Diode Ratings and Characteristics (T _C = 25°C) ^b						
Continuous Current	I _S				110	A
Pulsed Current	I _{SM}				350	
Forward Voltage ^a	V _{SD}	I _F = 110 A, V _{GS} = 0 V		1.0	1.5	V
Reverse Recovery Time	t _{rr}	I _F = 85 A, di/dt = 100 A/μs		75	120	ns
Peak Reverse Recovery Current	I _{RM(REC)}			3.5	7	A
Reverse Recovery Charge	Q _{rr}			0.13	0.30	μC

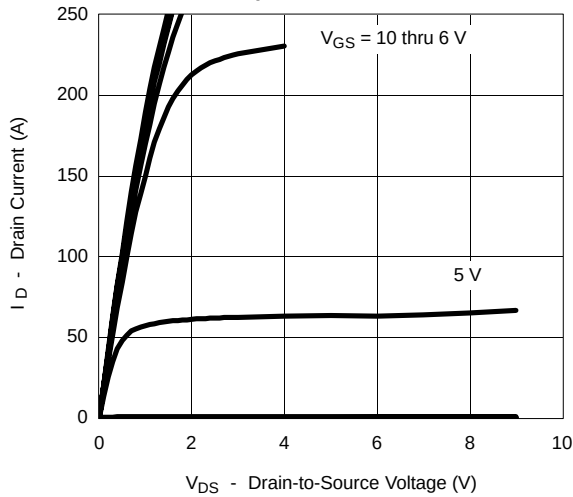
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

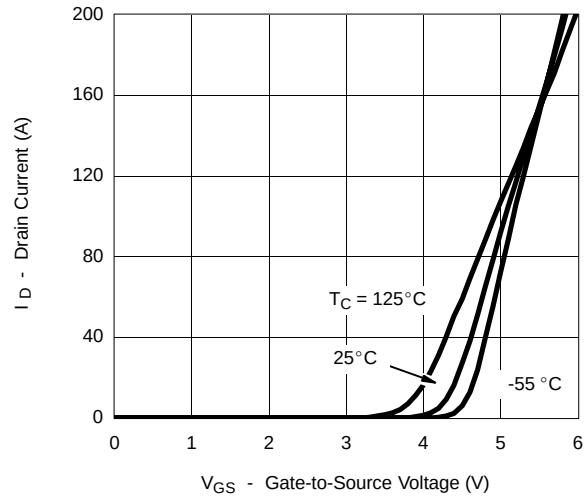


TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

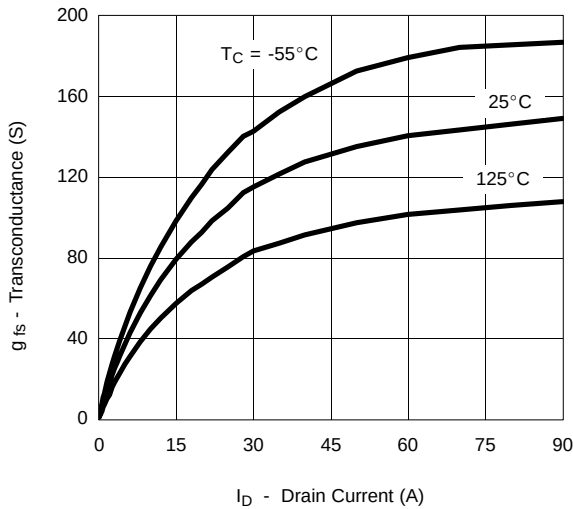
Output Characteristics



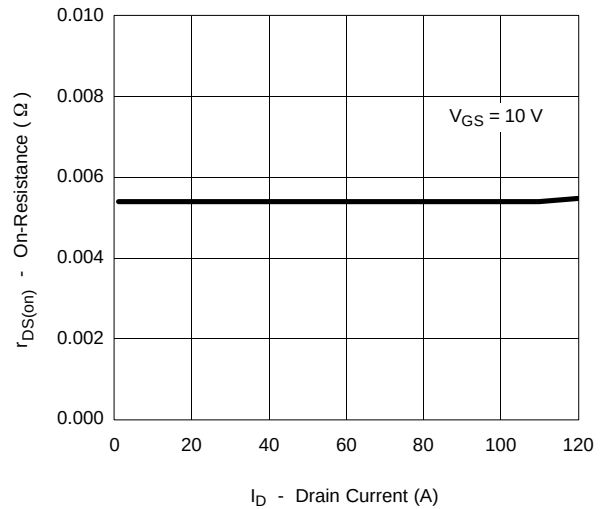
Transfer Characteristics



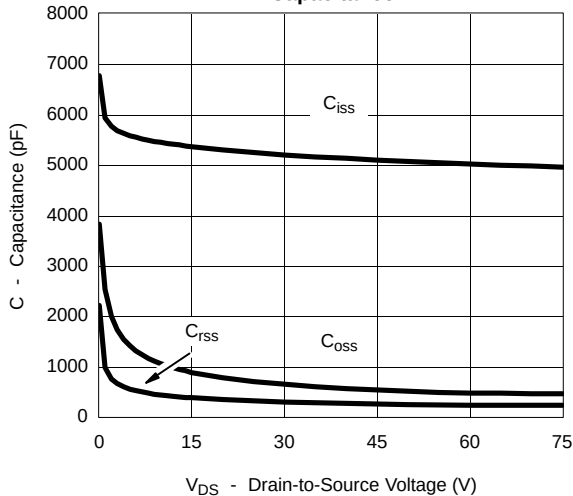
Transconductance



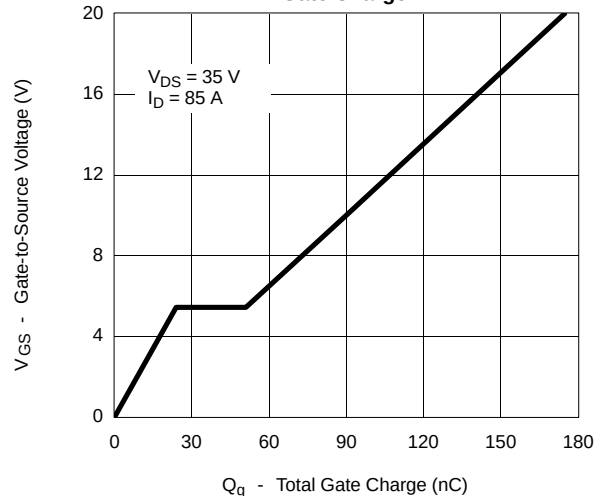
On-Resistance vs. Drain Current

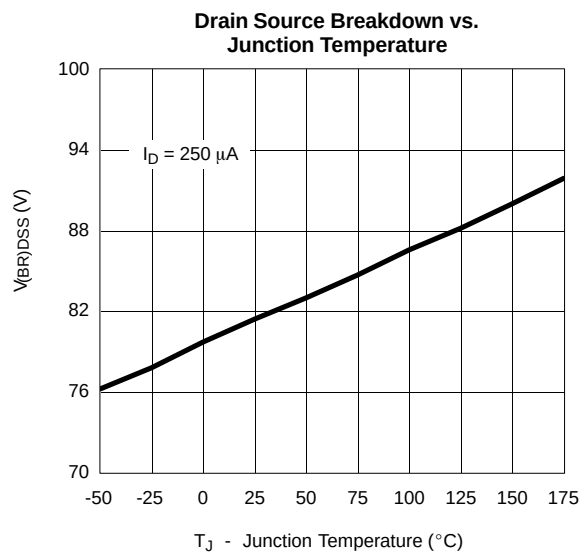
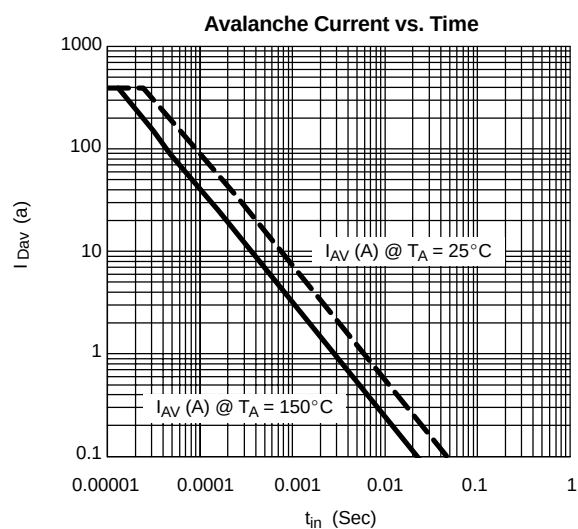
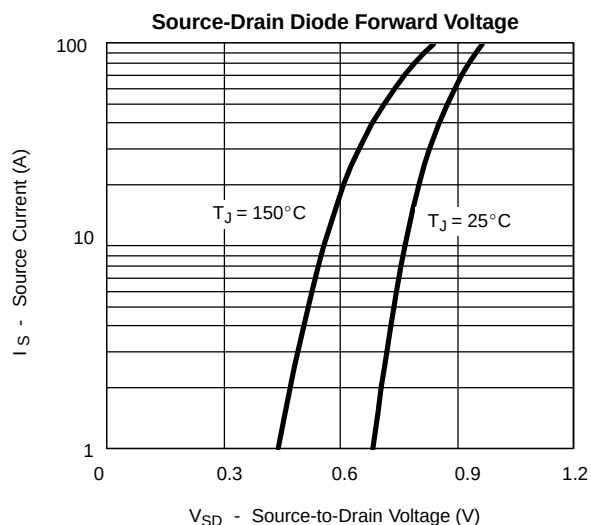
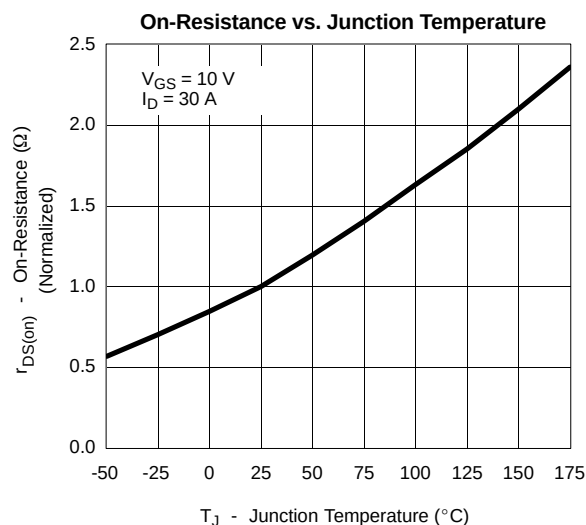


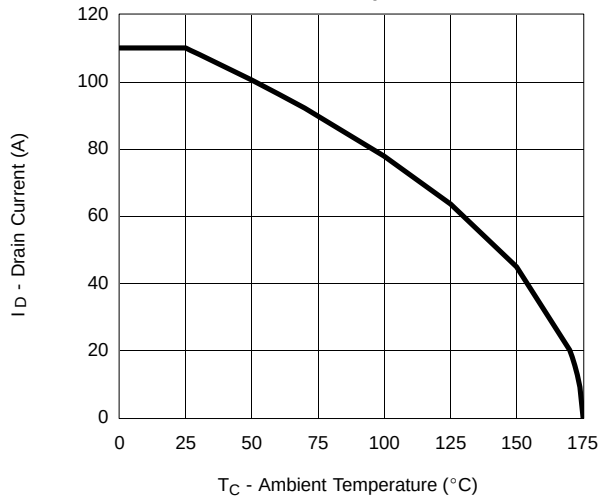
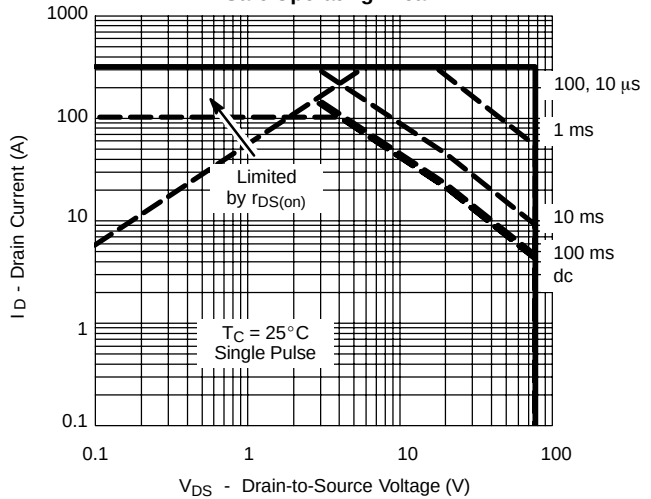
Capacitance



Gate Charge



TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

**THERMAL RATINGS****Maximum Avalanche and Drain Current
vs. Case Temperature****Safe Operating Area****Normalized Thermal Transient Impedance, Junction-to-Case**